

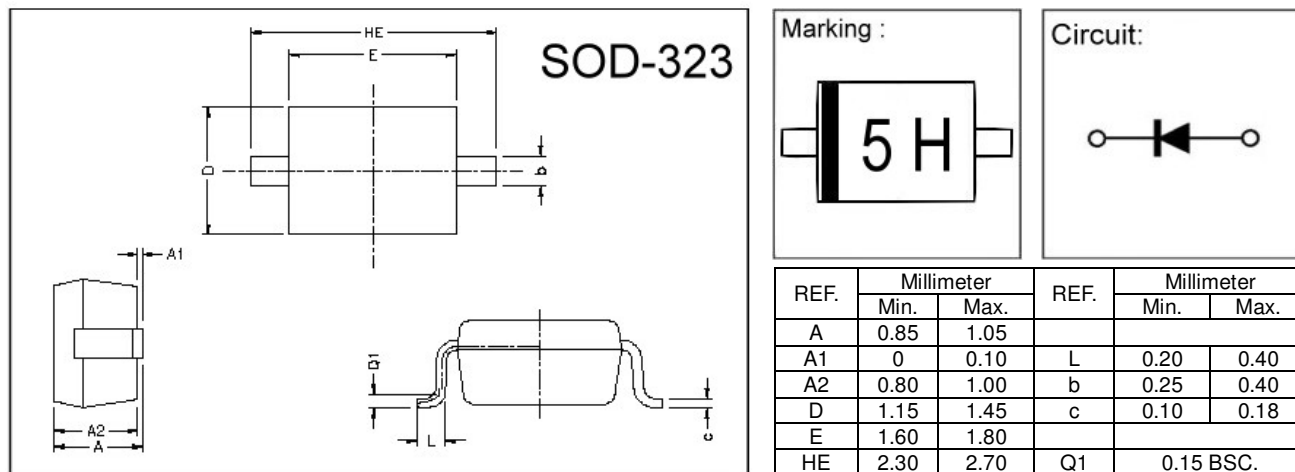
GD401SD

SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 30V, CURRENT 0.2A

Description

The GD401SD is high frequency rectification for switching power supply.

Package Dimensions



Absolute Maximum Ratings at TA = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+125	°C
Storage Temperature	T _{stg}	-55 ~ +125	°C
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	30	V
Maximum RMS Voltage	V _{RMS}	21	V
Maximum DC Blocking Voltage	V _{DC}	30	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	3.0	A
Typical Junction Capacitance between Terminal (Note 1)	C _J	40	pF
Maximum Average Forward Rectified Current	I _o	0.2	A
Total Power Dissipation	PD	225	mW

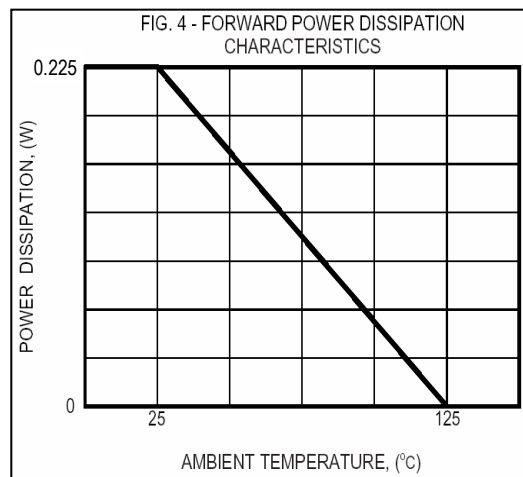
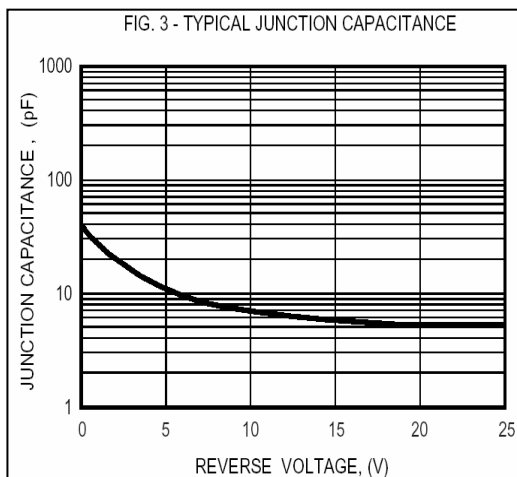
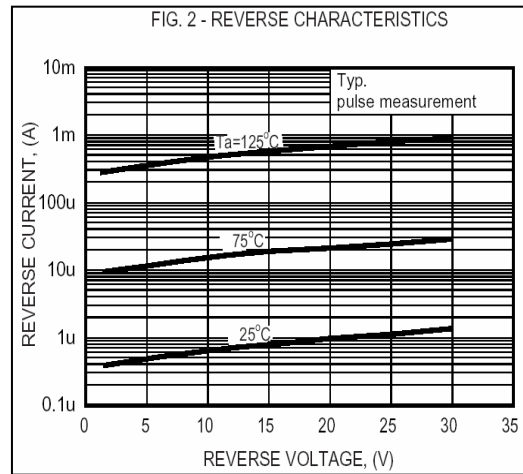
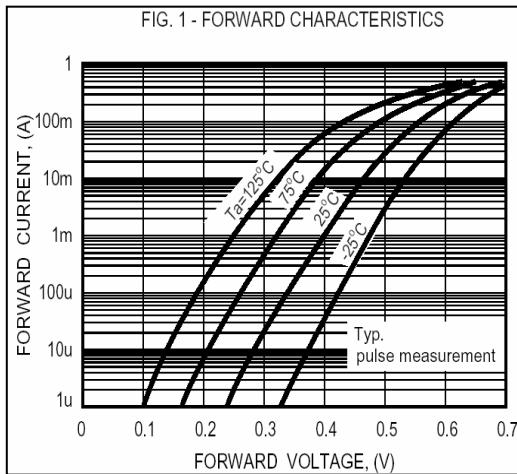
Electrical Characteristics (at TA = 25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V _{(BR)R}	30	-	-	V	IR=100μA
Maximum Instantaneous Forward Voltage	V _F	-	-	500	mV	IF=200mA
Maximum Average Reverse Current	I _R	-	-	50	μA	VR1=10V
		-	-	100	μA	VR2=30V

Notes: 1. Measured at 1.0 MHz and 0 reverse bias voltage.

2. ESD sensitive product handling required.

Characteristics Curve



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